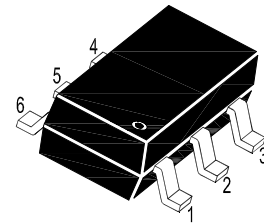
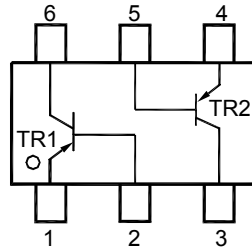


BC856D...BC858D

PNP Silicon Epitaxial Planar Transistor

for general purpose and switching applications



1. Emitter 2. Base 3. Collector
4. Emitter 5. Base 6. Collector
SOT-26 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	BC856D	80
		BC857D	50
		BC858D	30
Collector Emitter Voltage	$-V_{CEO}$	BC856D	65
		BC857D	45
		BC858D	30
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	100	mA
Peak Collector Current	$-I_{CM}$	100	mA
Total Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

TOP DYNAMIC



ISO14001 : 2004 Certificate No. 121505007
 ISO 9001 : 2008 Certificate No. 50114012
 OHSAS 18001 : 2007 Certificate No. 05131506006
 IECQ QC 080000 Certificate No. E04H1000714102

Dated: 10/01/2015 Rev: 01

BC856D...BC858D

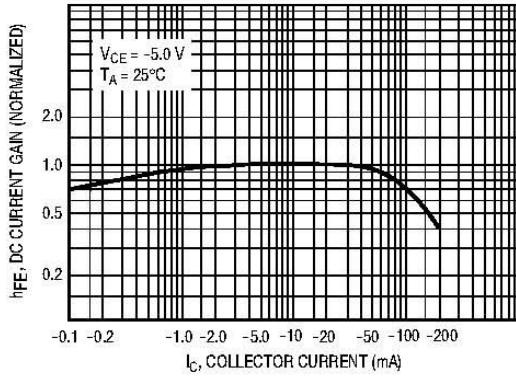
Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 5\text{ V}$, $-I_C = 2\text{ mA}$	BC856AD~BC858AD h_{FE}	125	250	-
	BC856BD~BC858BD h_{FE}	220	475	-
	BC856CD~BC858CD h_{FE}	420	800	-
Collector Base Voltage at $-I_C = 10\text{ }\mu\text{A}$	BC856D $-V_{CBO}$	80	-	V
	BC857D	50	-	
	BC858D	30	-	
Collector Emitter Voltage at $-I_C = 10\text{ mA}$	BC856D $-V_{CEO}$	65	-	V
	BC857D	45	-	
	BC858D	30	-	
Emitter Base Voltage at $-I_E = 1\text{ }\mu\text{A}$	$-V_{EBO}$	5	-	V
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	15	nA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	100	nA
Collector Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 0.5\text{ mA}$ $-I_C = 100\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$	-	0.3	V
		-	0.65	
Base Emitter Voltage at $-V_{CE} = 5\text{ V}$, $-I_C = 2\text{ mA}$ $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	$-V_{BE}$	0.6	0.75	V
		-	0.82	
Transition Frequency at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	100	-	MHz
Output Capacitance at $-V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$	C_{ob}	-	4.5	pF

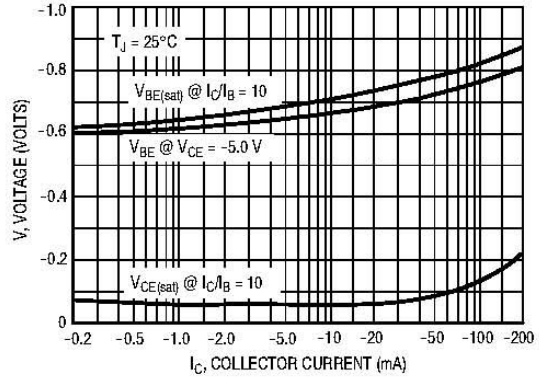
TOP DYNAMIC



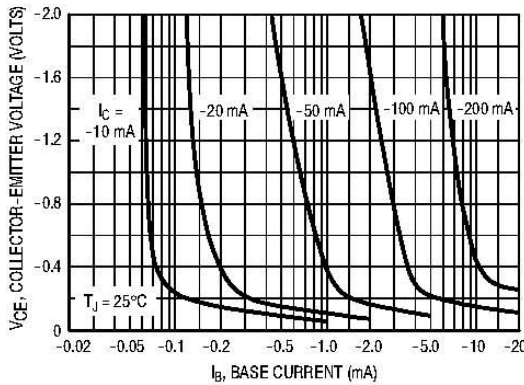
Dated: 10/01/2015 Rev: 01



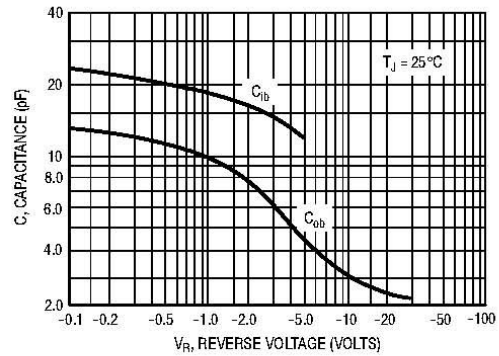
DC Current Gain



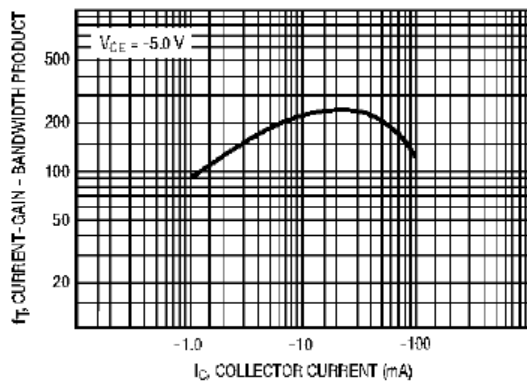
"On" Voltage



Collector Saturation Region



Capacitance

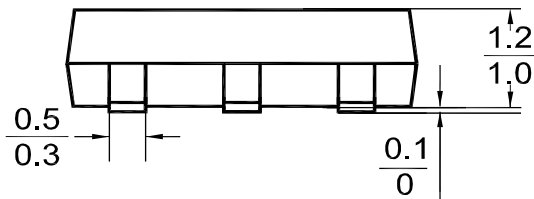
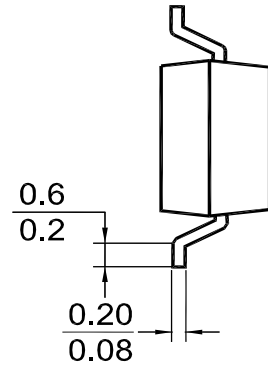
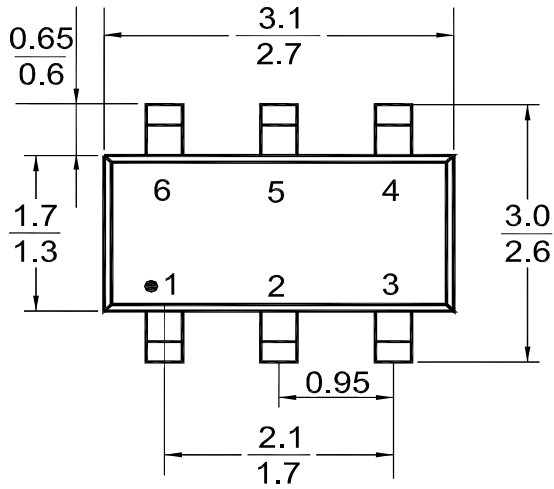


Current-Gain - Bandwidth Product

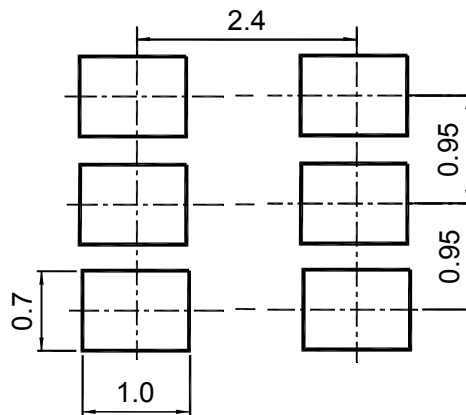
BC856D...BC858D

Package Outline Dimensions (Units: mm)

SOT-26



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-26	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

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